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(71)Applicant : **FUJI PHOTO FILM CO LTD.**

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(72)Inventor : **SATO KENICHIRO  
AOSO TOSHIKI**

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## (54) POSITIVE TYPE PHOTORESIST COMPOSITION

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a positive type resist composition having good PED, sensitivity and resolving power in the formation of contact holes in relation to lithography using a short-wavelength exposure light source for ultra-microfabrication and a positive type chemical amplification resist.

**SOLUTION:** The positive type resist composition contains (A) a resin containing repeating structural units each having a specified acid decomposable group and having the velocity of dissolution in an alkali developing solution increased by the action of an acid and (B) a compound which generates the acid when irradiated with active light or radiation.

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## LEGAL STATUS

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